

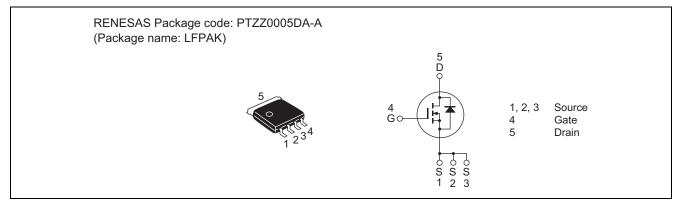
100V, 25A, 14m Ω max. Silicon N Channel Power MOS FET Power Switching

R07DS1059EJ0200 (Previous: REJ03G1888-0100) Rev.2.00 Apr 11, 2013

Features

- High speed switching
- Low drive current
- Low on-resistance
 - $R_{DS(on)} = 11 \text{ m}\Omega \text{ typ.}$ (at $V_{GS} = 10 \text{ V}$)
- Pb-free
- Halogen-free
- High density mounting

Outline



Absolute Maximum Ratings

			$(1a = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	100	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	25	A
Drain peak current	I _{D(pulse)} Note1	100	A
Body-drain diode reverse drain current	I _{DR}	25	A
Avalanche current	I _{AP} Note 2	25	A
Avalanche energy	E _{AS} Note 2	6.3	mJ
Channel dissipation	Pch Note3	65	W
Channel to Case Thermal Resistance	θch-C	1.92	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at L=10uH, Tch = 25°C, Rg \geq 50 Ω

3. Tc = 25°C



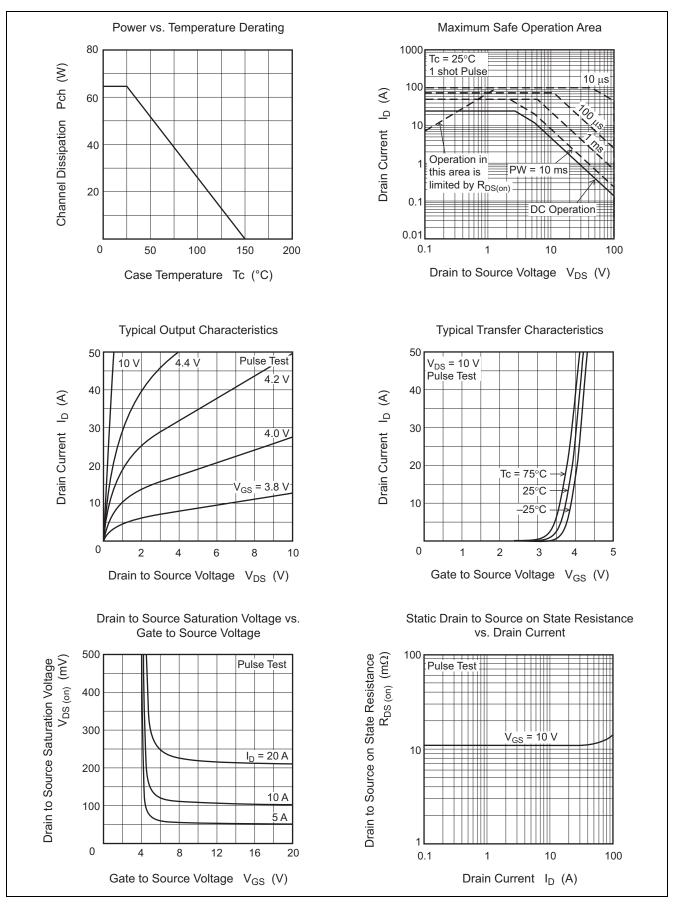
Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	100		—	V	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate to source leak current	I _{GSS}	_		±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Zero gate voltage drain current	I _{DSS}	_		1	μΑ	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$
Gate to source cutoff voltage	V _{GS(off)}	2.0		4.0	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	11	14	mΩ	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Forward transfer admittance	y _{fs}	_	42	—	S	$I_D = 12.5 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	3000	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	_	490	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	120	_	pF	
Gate Resistance	Rg	_	0.5	_	Ω	
Total gate charge	Qg	_	41	—	nC	$V_{DD} = 50 \text{ V}, \text{ V}_{GS} = 10 \text{ V},$
Gate to source charge	Qgs	_	13	—	nC	I _D = 25 A
Gate to drain charge	Qgd	_	7.5	_	nC	
Turn-on delay time	t _{d(on)}	_	16	_	ns	$V_{GS} = 10 \text{ V}, I_D = 12.5 \text{ A},$
Rise time	tr	_	4.5	_	ns	$\label{eq:VDD} \begin{array}{l} V_{DD} \cong 30 \ V, \ R_{L} = 2.4 \ \Omega, \\ Rg = 4.7 \ \Omega \end{array}$
Turn-off delay time	t _{d(off)}	_	36		ns	
Fall time	t _f	_	6.5		ns	
Body-drain diode forward voltage	V _{DF}	_	0.8	1.1	V	$I_F = 25 \text{ A}, V_{GS} = 0 \text{ V}^{Note4}$
Body-drain diode reverse recovery time	t _{rr}		52		ns	$I_F = 25 \text{ A}, V_{GS} = 0 \text{ V}$
						di _F / dt = 100 A/ μs

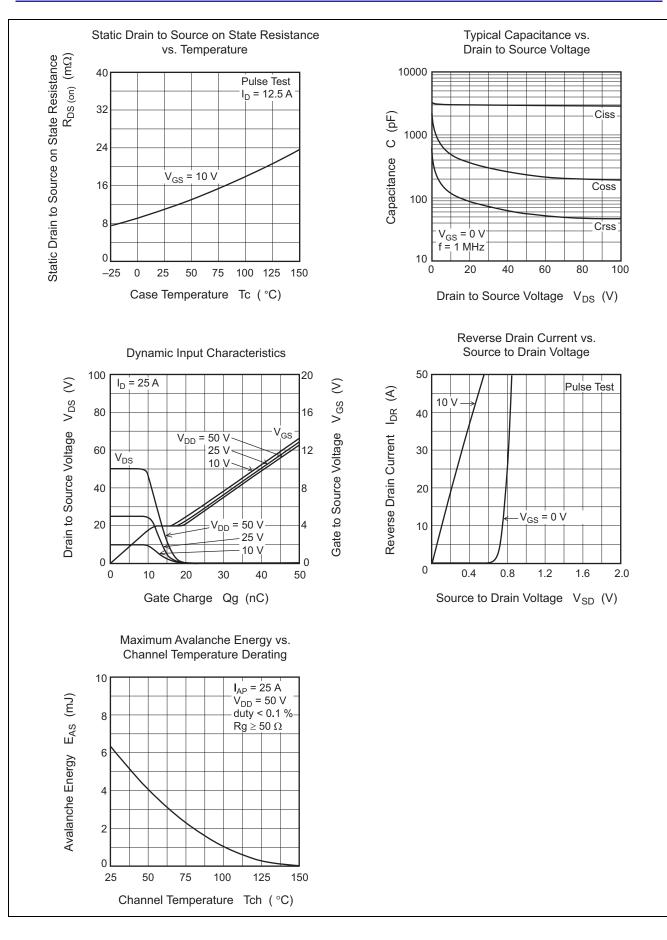
Notes: 4. Pulse test

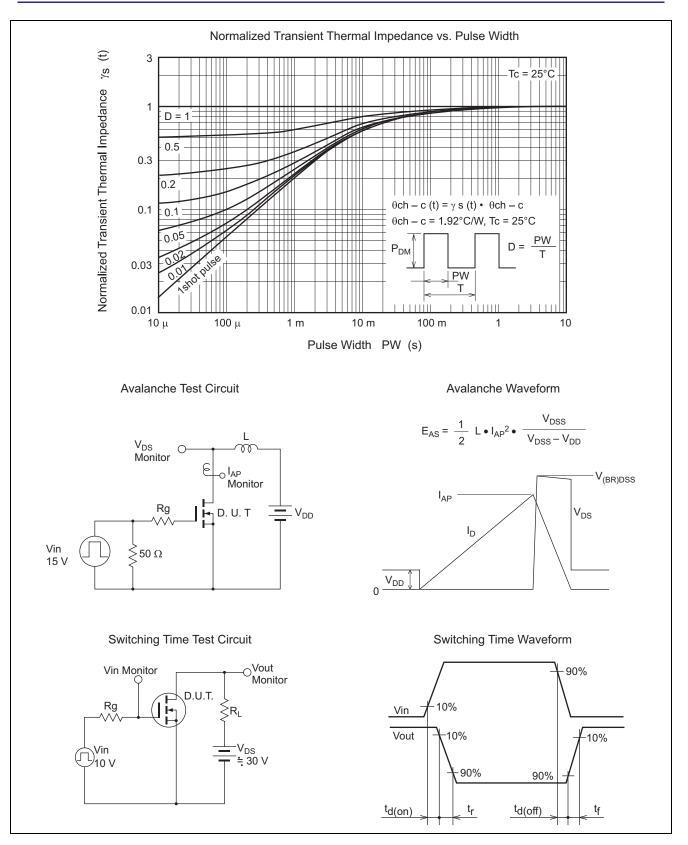


Main Characteristics



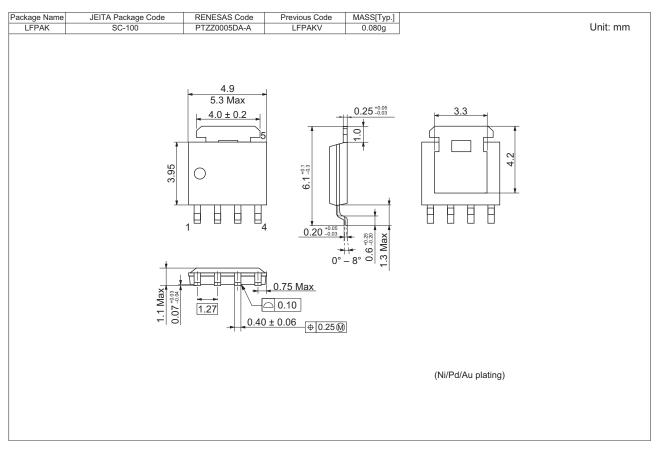








Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK1056DPB-00-J5	2500 pcs	Taping



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